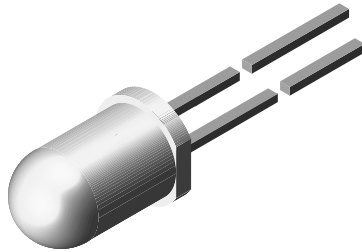


# High Speed Infrared Emitting Diode, 890 nm, GaAlAs Double Hetero



94 8389

## DESCRIPTION

TSHF6210 is an infrared, 890 nm emitting diode in GaAlAs double hetero (DH) technology with high radiant power and high speed, molded in a clear, untinted plastic package.

## FEATURES

- Package type: leaded
- Package form: T-1 $\frac{3}{4}$
- Dimensions (in mm):  $\varnothing$  5
- Peak wavelength:  $\lambda_p = 890$  nm
- High reliability
- High radiant power
- High radiant intensity
- Angle of half intensity:  $\varphi = \pm 10^\circ$
- Low forward voltage
- Suitable for high pulse current operation
- High modulation bandwidth:  $f_c = 12$  MHz
- Good spectral matching with Si photodetectors
- Compliant to RoHS directive 2002/95/EC and in accordance to WEEE 2002/96/EC
- Halogen-free according to IEC 61249-2-21 definition



**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**

## APPLICATIONS

- Infrared high speed remote control and free air data transmission systems with high modulation frequencies or high data transmission rate requirements
- Transmission systems according to IrDA requirements and for carrier frequency based systems (e.g. ASK/FSK - coded, 450 kHz or 1.3 MHz)
- Smoke-automatic fire detectors

## PRODUCT SUMMARY

COMPONENT	$I_e$ (mW/sr)	$\varphi$ (deg)	$\lambda_p$ (nm)	$t_r$ (ns)
TSHF6210	180	$\pm 10$	890	30

### Note

Test conditions see table "Basic Characteristics"

## ORDERING INFORMATION

ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM
TSHF6210	Bulk	MOQ: 4000 pcs, 4000 pcs/bulk	T-1 $\frac{3}{4}$

### Note

MOQ: minimum order quantity

## ABSOLUTE MAXIMUM RATINGS

PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Reverse voltage		$V_R$	5	V
Forward current		$I_F$	100	mA
Peak forward current	$t_p/T = 0.5, t_p = 100 \mu s$	$I_{FM}$	200	mA
Surge forward current	$t_p = 100 \mu s$	$I_{FSM}$	1.5	A
Power dissipation		$P_V$	160	mW
Junction temperature		$T_j$	100	$^\circ C$
Operating temperature range		$T_{amb}$	- 40 to + 85	$^\circ C$
Storage temperature range		$T_{stg}$	- 40 to + 100	$^\circ C$
Soldering temperature	$t \leq 5$ s, 2 mm from case	$T_{sd}$	260	$^\circ C$
Thermal resistance junction/ambient	J-STD-051, leads 7 mm soldered on PCB	$R_{thJA}$	230	K/W

### Note

$T_{amb} = 25 \text{ }^\circ C$ , unless otherwise specified

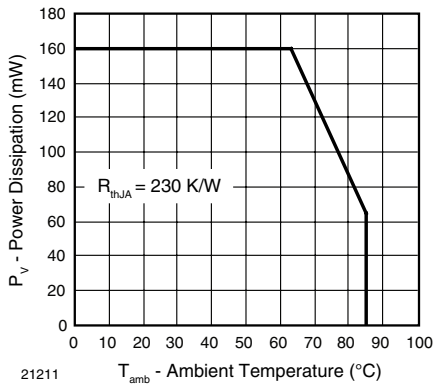


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

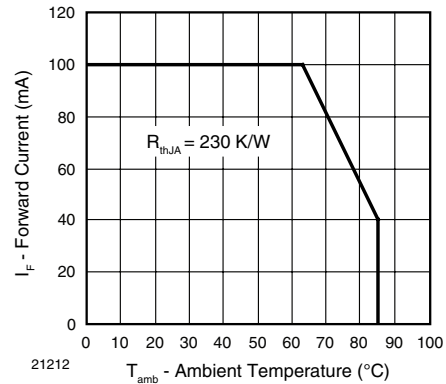


Fig. 2 - Forward Current Limit vs. Ambient Temperature

BASIC CHARACTERISTICS						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward voltage	$I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$	$V_F$		1.4	1.6	V
	$I_F = 1 \text{ A}, t_p = 100 \mu\text{s}$	$V_F$		2.3		V
Temperature coefficient of $V_F$	$I_F = 1 \text{ mA}$	$TK_{V_F}$		- 1.8		mV/K
Reverse current	$V_R = 5 \text{ V}$	$I_R$			10	$\mu\text{A}$
Junction capacitance	$V_R = 0 \text{ V}, f = 1 \text{ MHz}, E = 0$	$C_j$		125		pF
Radiant intensity	$I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$	$I_e$	120	180	360	mW/sr
	$I_F = 1 \text{ A}, t_p = 100 \mu\text{s}$	$I_e$		1800		mW/sr
Radiant power	$I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$	$\phi_e$		50		mW
Temperature coefficient of $\phi_e$	$I_F = 100 \text{ mA}$	$TK_{\phi_e}$		- 0.35		%/K
Angle of half intensity		$\varphi$		$\pm 10$		deg
Peak wavelength	$I_F = 100 \text{ mA}$	$\lambda_p$		890		nm
Spectral bandwidth	$I_F = 100 \text{ mA}$	$\Delta\lambda$		40		nm
Temperature coefficient of $\lambda_p$	$I_F = 100 \text{ mA}$	$TK_{\lambda_p}$		0.25		nm/K
Rise time	$I_F = 100 \text{ mA}$	$t_r$		30		ns
Fall time	$I_F = 100 \text{ mA}$	$t_f$		30		ns
Cut-off frequency	$I_{DC} = 70 \text{ mA}, I_{AC} = 30 \text{ mA pp}$	$f_c$		12		MHz
Virtual source diameter		$d$		3.7		mm

**Note**

$T_{amb} = 25 \text{ }^\circ\text{C}$ , unless otherwise specified

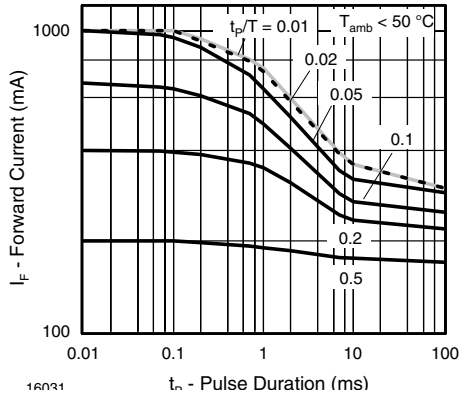
**BASIC CHARACTERISTICS**
 $T_{amb} = 25\text{ }^{\circ}\text{C}$ , unless otherwise specified


Fig. 3 - Pulse Forward Current vs. Pulse Duration

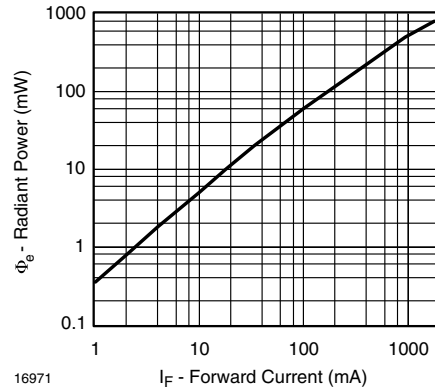


Fig. 6 - Radiant Power vs. Forward Current

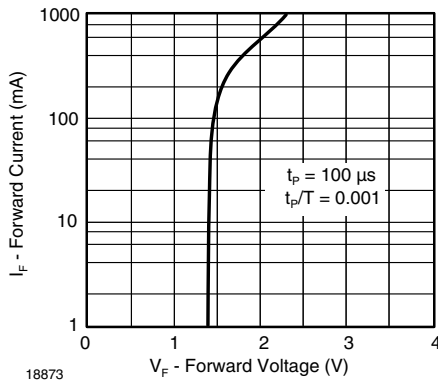


Fig. 4 - Forward Current vs. Forward Voltage

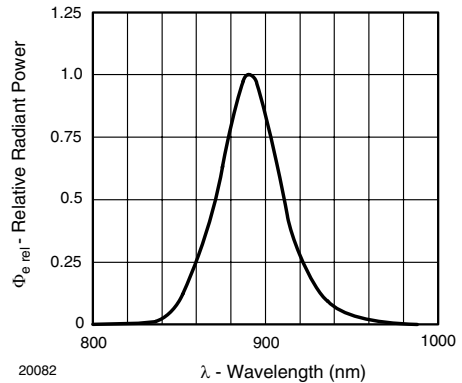


Fig. 7 - Relative Radiant Power vs. Wavelength

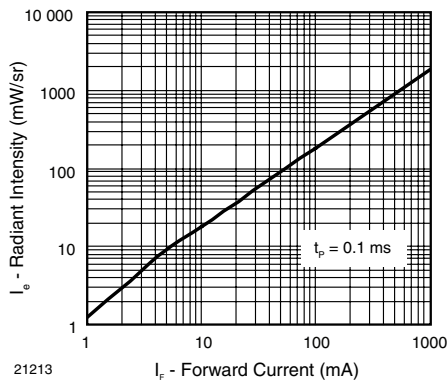


Fig. 5 - Radiant Intensity vs. Forward Current

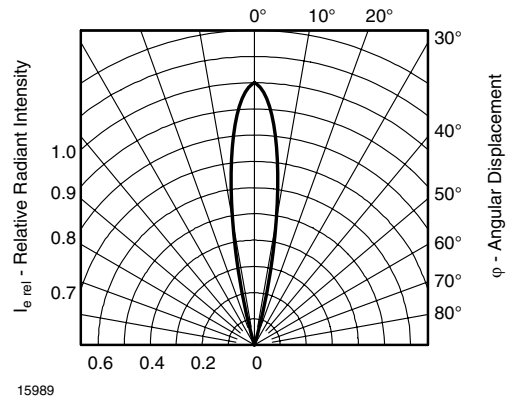


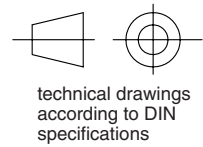
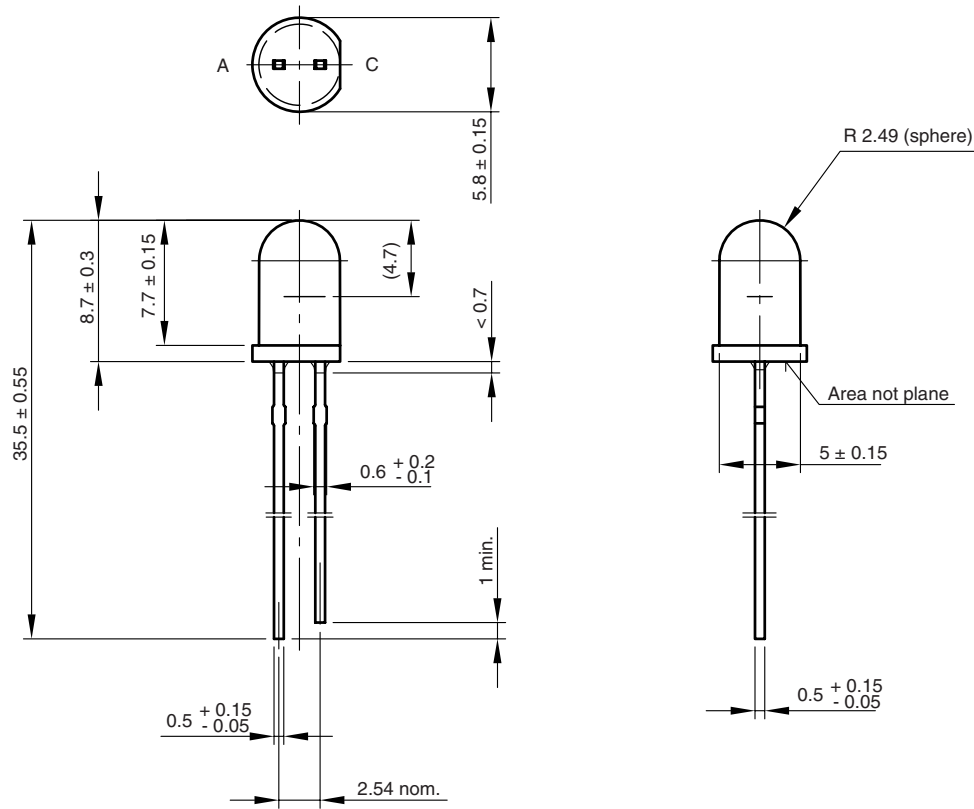
Fig. 8 - Relative Radiant Intensity vs. Angular Displacement

# TSHF6210



Vishay Semiconductors High Speed Infrared Emitting Diode,  
890 nm, GaAlAs Double Hetero

## PACKAGE DIMENSIONS in millimeters



6.544-5259.02-4  
Issue: 8; 19.05.09  
95 10917



## Disclaimer

All product specifications and data are subject to change without notice.

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